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providing a semiconductor substrate already completing a basic process of forming devices such as a field oxide, a source, a drain, and a gate thereon;

forming a dielectric layer used as an inter-layer dielectric on said semiconductor substrate, lapping said dielectric layer by means of a chemical mechanical polishing; and

forming a cap layer of a refractive index larger than 1.6 on said lapped dielectric layer.

Claim 6 is replaced with:

6. (Once Amended) The planarization method of inter-layer dielectrics as claimed in claim 1, wherein said cap layer is a silicon nitrogen-oxide layer capable of being transmitted by ultra-violet light.

Claim 9 should be replaced with:

9. (Once Amended) A planarization method of inter-metal dielectrics, comprising

the steps of:

providing a semiconductor substrate having a plurality of metal-interconnects formed thereon;

forming a dielectric layer used as an inter-metal dielectric on said substrate, lapping said dielectric layer by means of a chemical mechanical polishing; and

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forming a cap layer of a refractive index larger than 1.6 on said lapped dielectric layer.

Claim 17 is replaced with:

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17. (Once Amended) The planarization method of inter-metal dielectrics as claimed in claim 9, wherein said cap layer is a silicon nitrogen-oxide layer capable of being transmitted by ultra-violet light.